MARKING DIAGRAM

4M M=

SD Protection Diode

Low Capacitance ESD Protection Diode for High Speed Data Line

ESD7004, SZESD7004

The ESD7004 surge protection is designed to protect high speed data lines from ESD. Ultra-low capacitance and low ESD clamping voltage make this device an ideal solution for protecting voltage sensitive high speed data lines. The flow-through style package allows for easy PCB layout and matched trace lengths necessary to maintain consistent impedance between high speed differential lines such as USB 3.0 and HDMI.

Features

- Low Capacitance (0.4 pF Typical, I/O to GND)
- Protection for the Following IEC Standards: IEC 61000-4-2 (Level 4)
- Low ESD Clamping Voltage
- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- This is a Pb–Free Device

Typical Applications

- USB 3.0
- HDMI
- Display Port
- eSATA

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Operating Junction Temperature Range	TJ	-55 to +125	°C
Storage Temperature Range	T _{stg}	-55 to +150	°C
Lead Solder Temperature – Maximum (10 Seconds)	TL	260	°C
IEC 61000-4-2 Contact (ESD) IEC 61000-4-2 Air (ESD)	ESD ESD	±15 ±15	kV kV

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

See Application Note AND8308/D for further description of survivability specs.



Μ

CASE 517BB

4M	= Specific Device Code (tbd)
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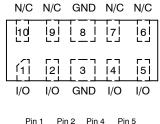
= Date Code

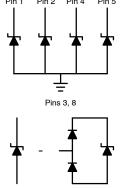
= Pb-Free Package

UDFN10

(Note: Microdot may be in either location)

PIN CONFIGURATION AND SCHEMATIC





ORDERING INFORMATION

Device	Package	Shipping
ESD7004MUTAG	UDFN10 (Pb-Free)	3000 / Tape & Reel
SZESD7004MUTAG	UDFN10 (Pb-Free)	3000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Reverse Working Voltage	V _{RWM}	I/O Pin to GND			5.0	V
Breakdown Voltage	V _{BR}	I _T = 1 mA, I/O Pin to GND 5.5			V	
Reverse Leakage Current	I _R	V _{RWM} = 5 V, I/O Pin to GND			1.0	μA
Clamping Voltage (Note 1)	V _C	I _{PP} = 1 A, I/O Pin to GND (8 x 20 μs pulse)		10	V	
Clamping Voltage (Note 2)	V _C	IEC61000-4-2, ±8 KV Contact	See Figures 1 and 2		V	
Clamping Voltage TLP (Note 3) See Figures 6 through 9	V _C	Ipp = 8 A Ipp = 16 A Ipp = -8 A Ipp = -16 A		11.4 15.6 -4.5 -8.1		
Junction Capacitance	CJ	V _R = 0 V, f = 1 MHz between I/O Pins	en I/O Pins 0.2		0.3	pF
Junction Capacitance	CJ	V _R = 0 V, f = 1 MHz between I/O Pins and GND 0.4 0		0.5	pF	

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise specified)

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Surge current waveform per Figure 5.

2. For test procedure see Figures 3 and 4 and application note AND8307/D.

3. ANSI/ESD STM5.5.1 – Electrostatic Discharge Sensitivity Testing using Transmission Line Pulse (TLP) Model. TLP conditions: $Z_0 = 50 \Omega$, $t_p = 100$ ns, $t_r = 4$ ns, averaging window; $t_1 = 30$ ns to $t_2 = 60$ ns.

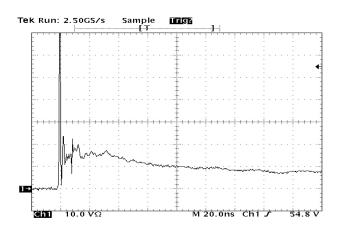


Figure 1. IEC61000-4-2 +8 KV Contact ESD **Clamping Voltage**

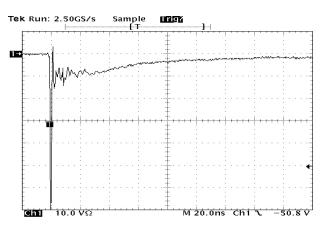
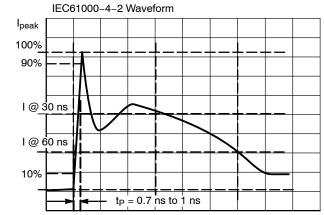
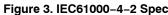


Figure 2. IEC61000-4-2 -8 KV Contact **Clamping Voltage**

IEC 61000-4-2 Spec.

Level	Test Volt- age (kV)	First Peak Current (A)	Current at 30 ns (A)	Current at 60 ns (A)
1	2	7.5	4	2
2	4	15	8	4
3	6	22.5	12	6
4	8	30	16	8





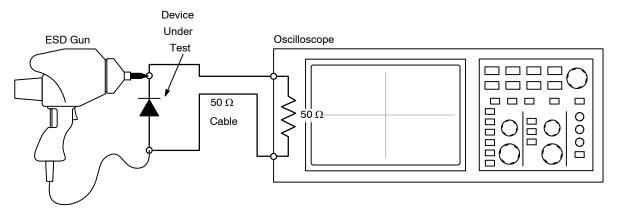


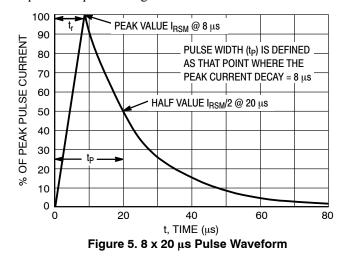
Figure 4. Diagram of ESD Clamping Voltage Test Setup

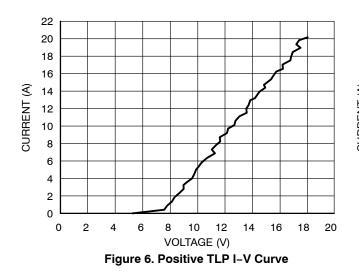
The following is taken from Application Note AND8308/D – Interpretation of Datasheet Parameters for ESD Devices.

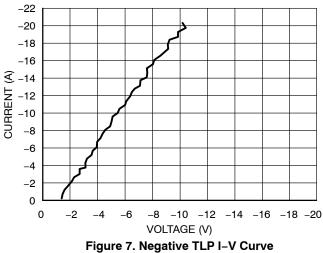
ESD Voltage Clamping

For sensitive circuit elements it is important to limit the voltage that an IC will be exposed to during an ESD event to as low a voltage as possible. The ESD clamping voltage is the voltage drop across the ESD protection diode during an ESD event per the IEC61000–4–2 waveform. Since the IEC61000–4–2 was written as a pass/fail spec for larger

systems such as cell phones or laptop computers it is not clearly defined in the spec how to specify a clamping voltage at the device level. **onsemi** has developed a way to examine the entire voltage waveform across the ESD protection diode over the time domain of an ESD pulse in the form of an oscilloscope screenshot, which can be found on the datasheets for all ESD protection diodes. For more information on how **onsemi** creates these screenshots and how to interpret them please refer to AND8307/D.







Transmission Line Pulse (TLP) Measurement

Transmission Line Pulse (TLP) provides current versus voltage (I–V) curves in which each data point is obtained from a 100 ns long rectangular pulse from a charged transmission line. A simplified schematic of a typical TLP system is shown in Figure 8. TLP I–V curves of ESD protection devices accurately demonstrate the product's ESD capability because the 10s of amps current levels and

under 100 ns time scale match those of an ESD event. This is illustrated in Figure 9 where an 8 kV IEC 61000–4–2 current waveform is compared with TLP current pulses at 8 A and 16 A. A TLP I–V curve shows the voltage at which the device turns on as well as how well the device clamps voltage over a range of current levels. A typical TLP I–V curve for the ESD7004 is shown in Figures 6 and 7.

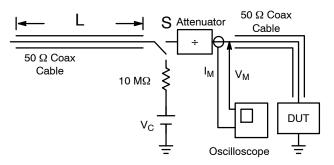


Figure 8. Simplified Schematic of a Typical TLP System

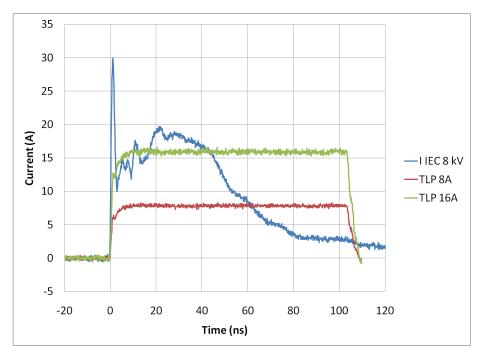
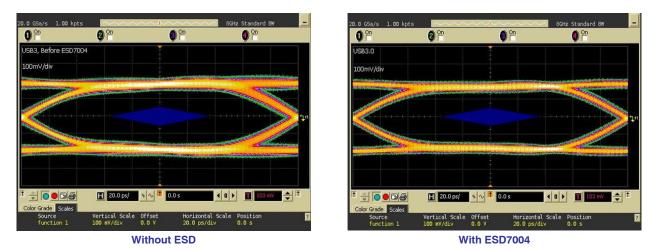
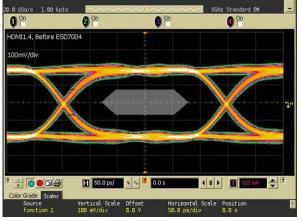
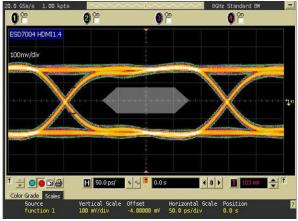


Figure 9. Comparison Between 8 kV IEC 61000-4-2 and 8 A and 16 A TLP Waveforms









Without ESD

With ESD7004



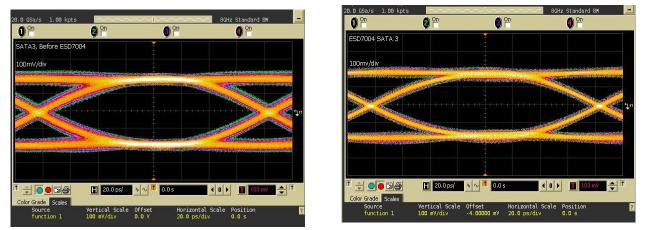
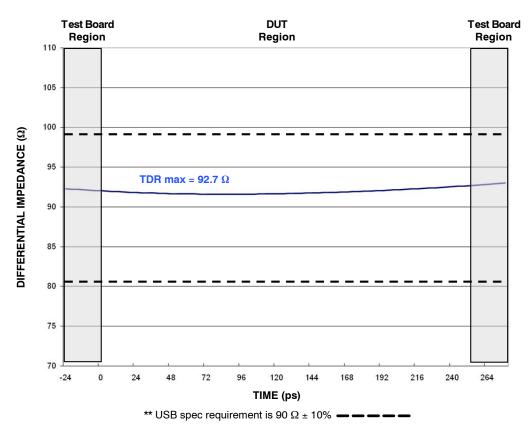






Figure 12. ESATA3.0 Eye Diagram with and without ESD7004. 6 Gb/s, 400 mV_{PP}





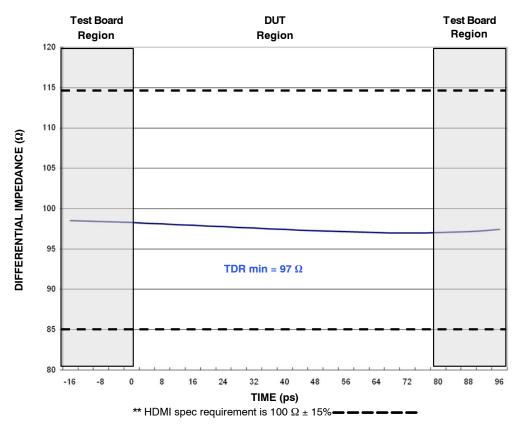
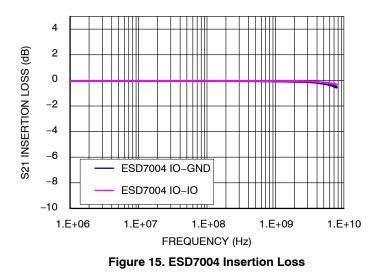


Figure 14. HDMI TDR Measurement. 100 Ω Differential Impedance Target, 200 ps Rise Time



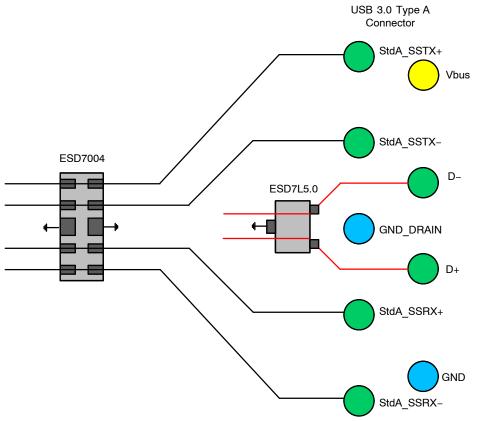
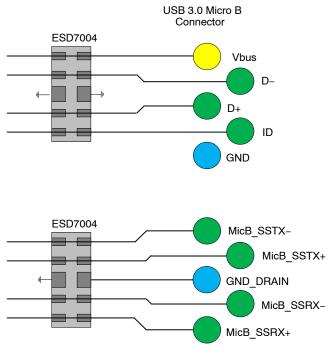


Figure 16. USB3.0 Standard A Connector Layout Diagram





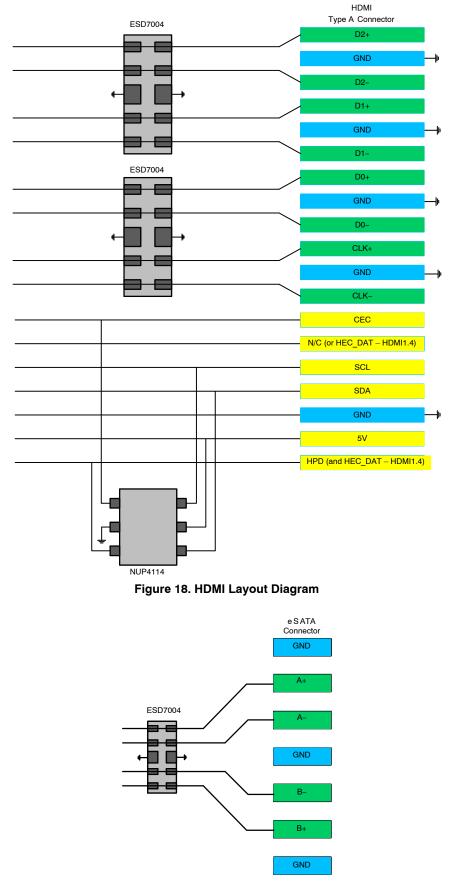
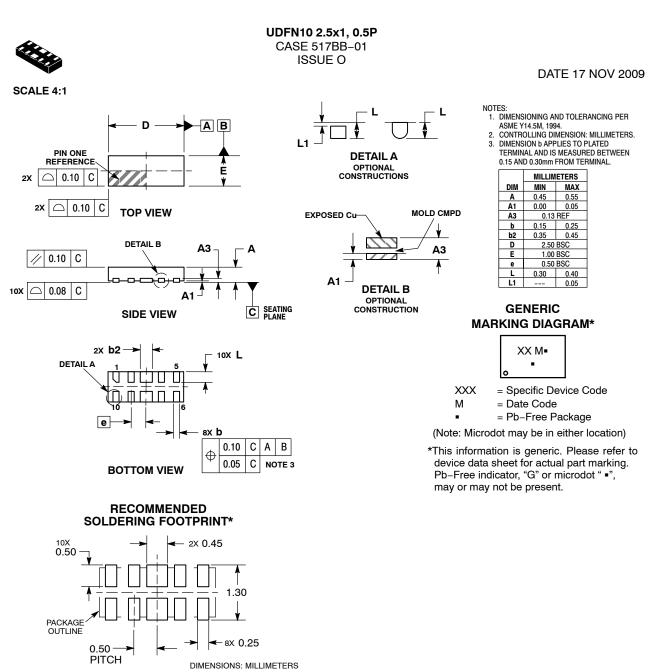


Figure 19. eSATA Layout Diagram





*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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